NCE N-Channel Super Trench II Power MOSFET

Description

The NCEP25N10AK uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

General Features

- V_{DS} =100V,I_D =35A
 - $R_{DS(ON)}$ =21m Ω (typical) @ V_{GS} =10V
 - $R_{DS(ON)}$ =26m Ω (typical) @ V_{GS} =4.5V

• Excellent gate charge x R_{DS(on)} product(FOM)

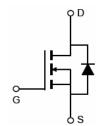
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating

100% UIS TESTED! 100% ΔVds TESTED!

TO-252-2L



Top View



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP25N10AK	NCEP25N10AK	TO-252-2L	-	-	-

Absolute Maximum Ratings (T_C=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	100	V
Gate-Source Voltage	V _G s	±20	V
Drain Current-Continuous	I _D	35	Α
Drain Current-Continuous(T _C =100℃)	I _D (100℃)	25	Α
Pulsed Drain Current	I _{DM}	140	Α
Maximum Power Dissipation	P _D	105	W
Derating factor		0.7	W/℃
Single pulse avalanche energy (Note 5)	E _{AS}	97	mJ
Operating Junction and Storage Temperature Range	T_{J} , T_{STG}	-55 To 175	$^{\circ}$

Thermal Characteristic

Thermal Resistance,Junction-to-Case ^(Note 2)	R _{eJC}	1.43	°C/W
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NCEP25N10AK

Electrical Characteristics (T_C=25°C unless otherwise noted)

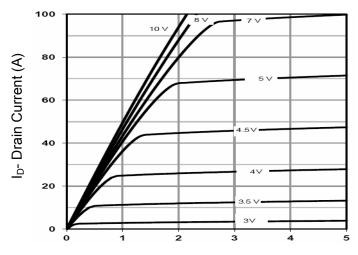
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	100		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS} , I_{D} =250 μ A	1.1	1.7	2.5	V
Drain-Source On-State Resistance	D	V _{GS} =10V, I _D =20A	-	21	25	mΩ
Diain-Source On-State Resistance	n-State Resistance $R_{DS(ON)}$ V_{GS} =4.5V, I_D =20A - 26 30 conductance g_{FS} V_{DS} =5V, I_D =20A - 19 - acteristics (Note4)	30	mΩ			
Forward Transconductance	g FS	V_{DS} =5 V , I_D =20 A	1-	19	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}	V 50/V 0	-	1317.6	-	PF
Output Capacitance	Coss	V _{DS} =50V,V _{GS} =0V F=1.0MHz	-	123.9	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0WH12	-	19.3	-	PF
Switching Characteristics (Note 4)		.15				
Turn-on Delay Time	t _{d(on)}	O_{2}	-	13	-	nS
Turn-on Rise Time	t _r	V_{DD} =50V, I_{D} =20A	-	15	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{G} =3 Ω	-	22	-	nS
Turn-Off Fall Time	t _f		-	6	-	nS
Total Gate Charge	Q_{g}	V _{DS} =50V,I _D =20A,	-	27.6	-	nC
Gate-Source Charge	Q _{gs}	V_{DS} =30V, I_D =20A, V_{GS} =10V	-	5.5		nC
Gate-Drain Charge	Q_{gd}	V GS-10 V	-	6.9		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V _{GS} =0V,I _S =20A	-		1.2	V
Diode Forward Current (Note 2)	I _S		-	-	35	Α
Reverse Recovery Time	t _{rr}	$T_J = 25^{\circ}C, I_F = 20A$	-	40	-	nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	-	85	-	nC

Notes:

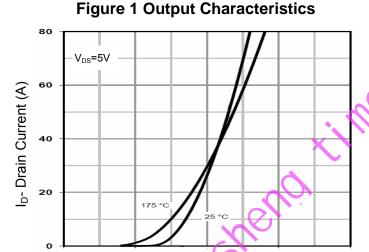
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, $t \le 10$ sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25 $^{\circ}\text{C}$,VDD=50V,VG=10V,L=0.5mH,Rg=25 Ω



Typical Electrical and Thermal Characteristics



Vds Drain-Source Voltage (V)



Vgs Gate-Source Voltage (V)

Figure 2 Transfer Characteristics

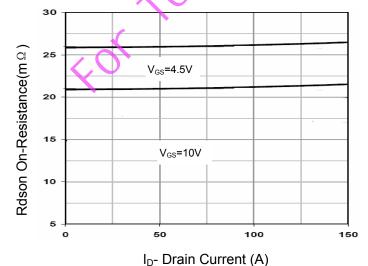


Figure 3 Rdson- Drain Current

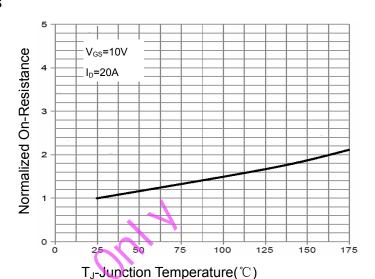


Figure 4 Rdson-Junction Temperature

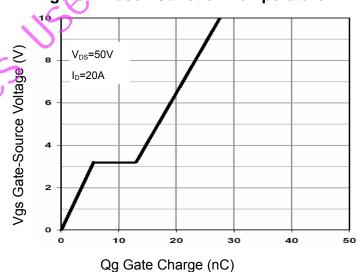
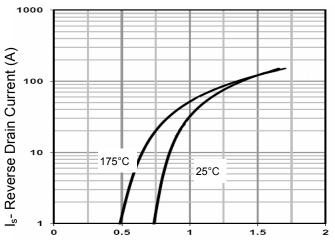


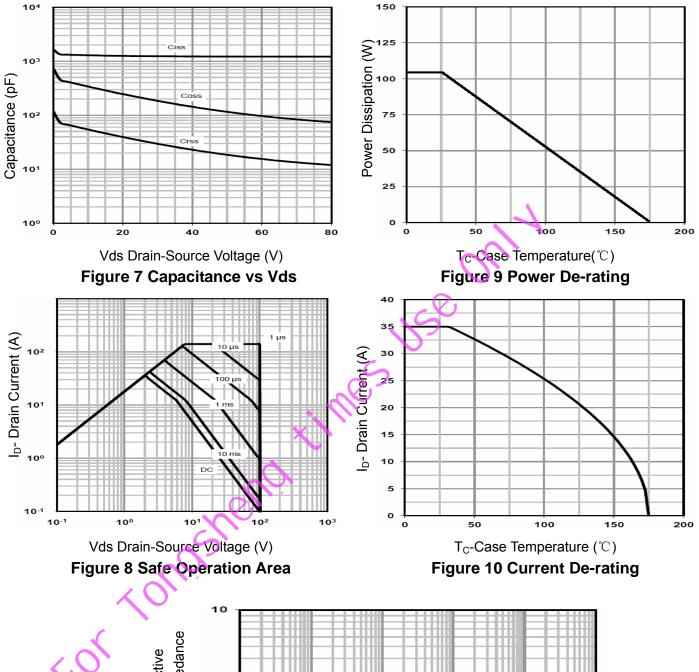
Figure 5 Gate Charge



Vsd Source-Drain Voltage (V)

Figure 6 Source- Drain Diode Forward





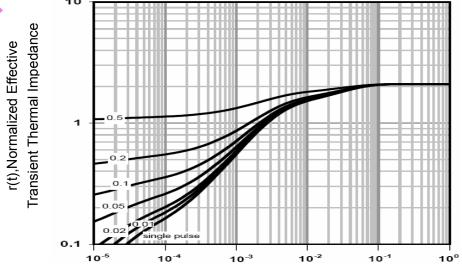
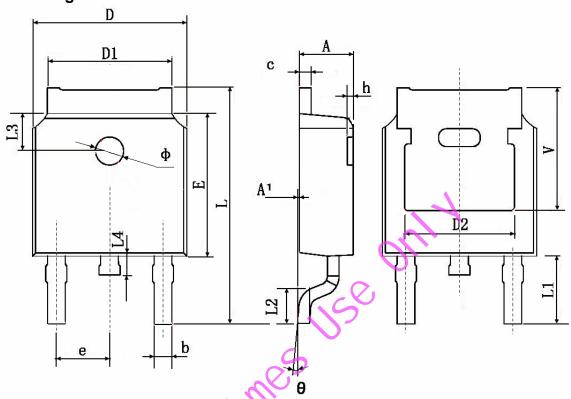


Figure 11 Normalized Maximum Transient Thermal Impedance

Square Wave Pluse Duration(sec)



TO-252-2L Package Information



Cumbal	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
Α	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	4.8	3 TYP.	0.190 TYP.		
E	6.000	6.200	0.236	0.244	
e 🎸	2.186	2.386	0.086	0.094	
<u> </u>	9.800	10.400	0.386	0.409	
L1	2.90	0 TYP.	0.114 TYP.		
L2	1.400	1.700	0.055	0.067	
L3	1.60	0 TYP.	0.063 TYP.		
L4	0.600	1.000	0.024	0.039	
Ф	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.35	0 TYP.	0.211 TYP.		

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NCEP25N10AK

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